

SANYONo. $\times$ 5084A**LC322270J, T-70/80****2 MEG (131072 words $\times$ 16 bits) DRAM
Fast Page Mode, Byte Write****Preliminary****Overview**

The LC322270J, T is a CMOS dynamic RAM operating on a single 5 V power source and having a 131072 words $\times$ 16 bits configuration. Equipped with large capacity capabilities, high-speed transfer rates and low power dissipation, this series is suited for a wide variety of applications ranging from computer main memory and expansion memory to commercial equipment.

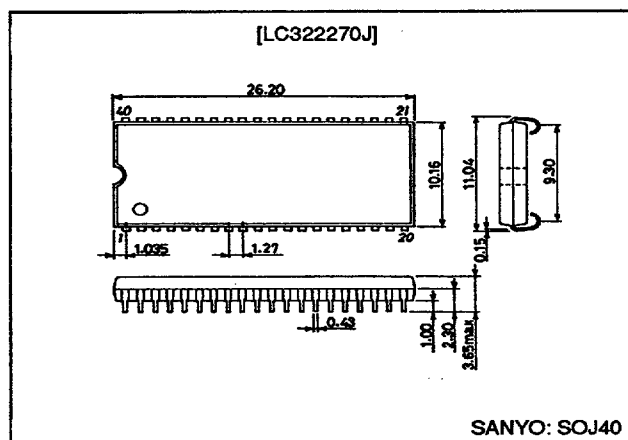
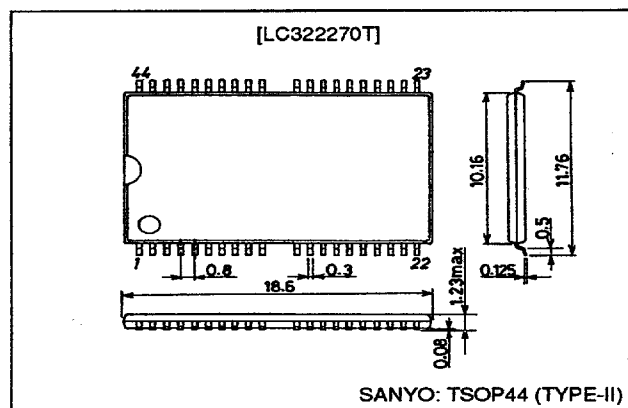
Address input utilizes a multiplexed address bus which permits it to be enclosed in a compact plastic package of SOJ 40-pin and TSOP 44-pin. Refresh rates are within 8 ms with 512 row address (A0 to A7, A8R) selection and support Row Address Strobe ($\overline{\text{RAS}}$)-only refresh, Column Address Strobe ($\overline{\text{CAS}}$)-before- $\overline{\text{RAS}}$ refresh and hidden refresh settings. There are functions such as fast page mode, read-modify-write and byte write. The pin assignment follows the JEDEC 4M DRAM (262144 words $\times$ 16 bits, 1CAS/2WE type) standard pinouts.

Features

- 131072 words $\times$ 16 bits configuration.
- Single 5 V $\pm$ 10% power supply.
- All input and output (I/O) TTL compatible.
- Supports fast page mode, read-modify-write and byte write.
- Supports output buffer control using early write and Output Enable ($\overline{\text{OE}}$) control.
- 8 ms refresh using 512 refresh cycles.
- Supports $\overline{\text{RAS}}$ -only refresh, $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh and hidden refresh.
- Follows the JEDEC 4M DRAM (262144 words $\times$ 16 bits, 1CAS/2WE type) standard pinouts.
- Package:
SOJ 40-pin (400 mil) plastic package: LC322270J
TSOP 44-pin (400 mil) plastic package: LC322270T
- $\overline{\text{RAS}}$ access time/column address access time/ $\overline{\text{CAS}}$ access time/cycle time/power dissipation.

Package Dimensions

unit: mm

**3200-SOJ40****3207-TSOP44**

unit: mm

Parameter		LC322270J, T	
		-70	-80
$\overline{\text{RAS}}$ access time		70 ns	80 ns
Column address access time		35 ns	45 ns
$\overline{\text{CAS}}$ access time		20 ns	30 ns
Cycle time		130 ns	150 ns
Power dissipation (max.)	During operation	688 mW	633 mW
	During standby	5.5 mW (CMOS level)/11 mW (TTL level)	

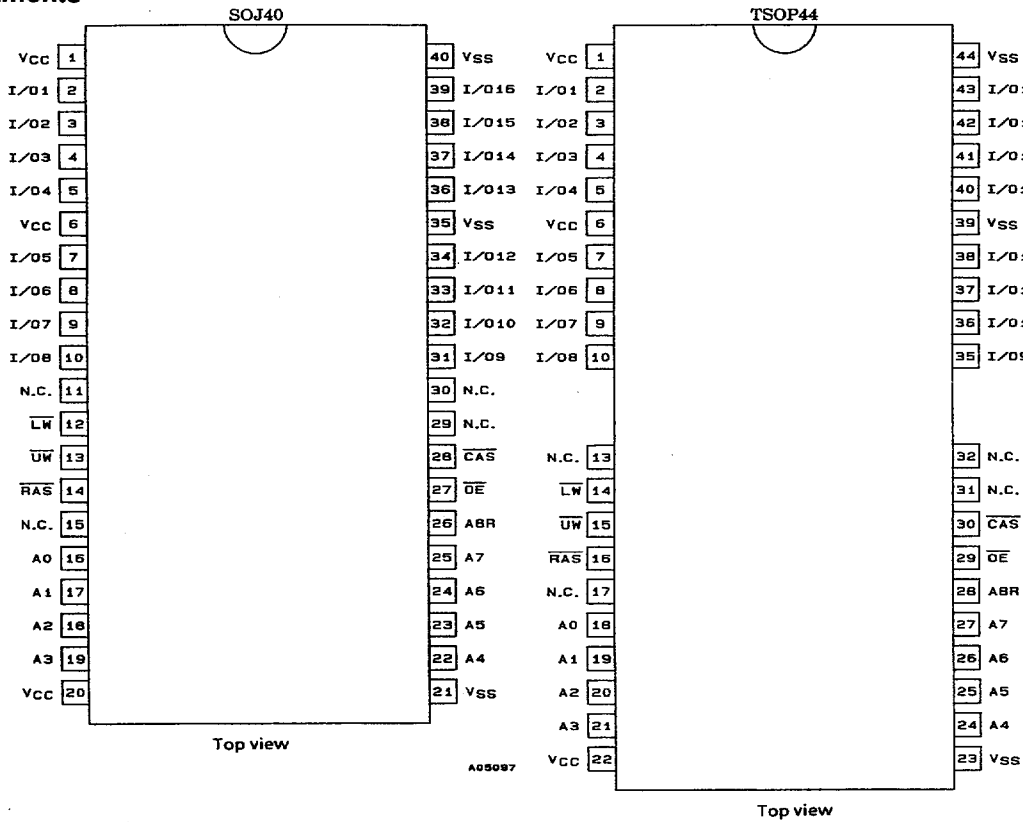
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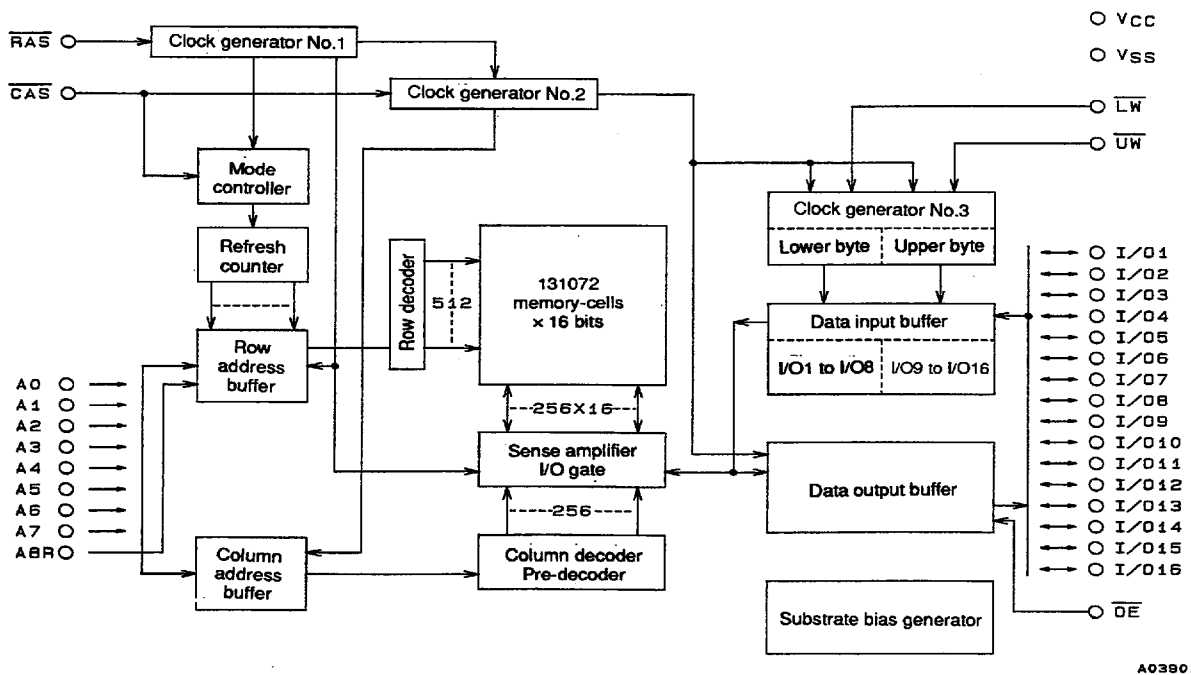
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32896HA (OT)/33195TH (OT) No. 5084-1/28

Pin Assignments



Block Diagram



Specifications

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit	Note
Maximum supply voltage	V_{CC} max	-1.0 to +7.0	V	1
Input voltage	V_{IN}	-1.0 to +7.0	V	1
Output voltage	V_{OUT}	-1.0 to +7.0	V	1
Allowable power dissipation	LC322270J	800	mW	1
	LC322270T	700		
Output short-circuit current	I_{OUT}	50	mA	1
Operating temperature range	T_{opr}	0 to +70	°C	1
Storage temperature range	T_{stg}	-55 to +150	°C	1

Note: 1. Stresses greater than the above listed maximum values may result in damage to the device.

DC Recommended Operating Ranges at $T_a = 0$ to +70°C

Parameter	Symbol	min	typ	max	Unit	Note
Power supply voltage	V_{CC}	4.5	5.0	5.5	V	2
Input high level voltage	V_{IH}	2.4		6.5	V	2
Input low level voltage (A0 to A7, A8R, RAS, CAS, $\overline{UW}$, LW, $\overline{OE}$)	V_{IL}	-1.0*		+0.8	V	2
Input low level voltage (I/O1 to I/O16)	V_{IL}	-0.5*		+0.8	V	2

Note: 2. All voltages are referenced to V_{SS} .

*: -2.0 V when pulse width is less than 20 ns.

DC Electrical Characteristics at $T_a = 0$ to +70°C, $V_{CC} = 5\text{ V} \pm 10\%$

Parameter	Symbol	Conditions	LC322270J, T				Unit	Note
			-70		-80			
			min	max	min	max		
Operating current (Average current during operation)	I _{CC1}	$\overline{RAS}$, $\overline{CAS}$, address cycling: t _{RC} = t _{RC} min		125		115	mA	3, 4, 5
Standby current	I _{CC2}	$\overline{RAS} = \overline{CAS} = V_{IH}$		2		2	mA	
$\overline{RAS}$ -only refresh current	I _{CC3}	$\overline{RAS}$ cycling, $\overline{CAS} = V_{IH}$: t _{RC} = t _{RC} min		125		115	mA	3, 5
Fast page mode current	I _{CC4}	$\overline{RAS} = V_{IL}$, $\overline{CAS}$, address cycling: t _{PC} = t _{PC} min		115		90	mA	3, 4, 5
Standby current	I _{CC5}	$\overline{RAS} = \overline{CAS} = V_{CC} - 0.2\text{ V}$		1		1	mA	
$\overline{CAS}$ -before- $\overline{RAS}$ refresh current	I _{CC6}	$\overline{RAS}$, $\overline{CAS}$ cycling: t _{RC} = t _{RC} min		125		115	mA	3
Input leakage current	I _{IL}	0 V ≤ V _{IN} ≤ 6.5 V, pins other than test pin = 0 V	-10	+10	-10	+10	μA	
Output leakage current	I _{OL}	D _{OUT} disable, 0 V ≤ V _{OUT} ≤ 5.5 V	-10	+10	-10	+10	μA	
Output high level voltage	V _{OH}	I _{OUT} = -2.5 mA	2.4		2.4		V	
Output low level voltage	V _{OL}	I _{OUT} = 2.1 mA		0.4		0.4	V	

Note: 3. All current values are measured at minimum cycle rate. Since current flows immoderately, if cycle time is longer than shown here, current value becomes smaller.

4. I_{CC1} and I_{CC4} are dependent on output loads. Maximum values for I_{CC1} and I_{CC4} represent values with output open.

5. Address change is less than or equal to one time during $\overline{RAS} = V_{IL}$. Concerning I_{CC4} , it is less than or equal to one time during 1 cycle (t_{PC}).

LC322270J, T-70/80

AC Electrical Characteristics at Ta = 0 to +70°C, V_{CC} = 5 V ± 10% (Notes 6, 7 and 8)

Parameter	Symbol	LC322270J,T				Unit	Note
		-70		-80			
		min	max	min	max		
Random read, write cycle time	t _{RC}	130		150		ns	
Read-write/read-modify-write cycle time	t _{RWC}	190		200		ns	
Fast page mode cycle time	t _{PC}	45		55		ns	
Fast page mode read-write/read-modify-write cycle time	t _{PRWC}	95		100		ns	
RAS access time	t _{RAC}		70		80	ns	9, 14, 15
CAS access time	t _{CAC}		20		30	ns	9, 14
Column address access time	t _{AA}		35		45	ns	9, 15
CAS precharge access time	t _{CPA}		40		50	ns	9
Output low-impedance time from CAS low	t _{CLZ}	0		0		ns	9
Output buffer turn-off delay time	t _{OFF}	0	20	0	20	ns	10
Rise, fall time	t _T	3	50	3	50	ns	
RAS precharge time	t _{RP}	50		60		ns	
RAS pulse width	t _{RAS}	70	10000	80	10000	ns	
RAS pulse width for fast page mode cycle only	t _{RASP}	70	100000	80	100000	ns	
RAS hold time	t _{RSH}	20		30		ns	
CAS hold time	t _{CSH}	70		80		ns	
CAS pulse width	t _{CAS}	20	10000	30	10000	ns	
RAS to CAS delay time	t _{RCD}	25	50	25	50	ns	14
RAS to column address delay time	t _{RAD}	17	35	17	35	ns	15
CAS to RAS precharge time	t _{CRP}	10		10		ns	
CAS precharge time	t _{CP}	10		10		ns	
Row address setup time	t _{ASR}	0		0		ns	
Row address hold time,	t _{RAH}	12		12		ns	
Column address setup time	t _{ASC}	0		0		ns	
Column address hold time	t _{CAH}	15		20		ns	
Column address hold time referenced to RAS	t _{AR}	50		60		ns	
Column address to RAS lead time	t _{RAL}	40		45		ns	
Read command setup time	t _{RCS}	0		0		ns	
Read command hold time referenced to CAS	t _{RCH}	0		0		ns	11
Read command hold time referenced to RAS	t _{RRH}	0		0		ns	11
Write command hold time	t _{WCH}	15		15		ns	
Write command hold time referenced to RAS	t _{WCR}	50		60		ns	
Write command pulse width	t _{WP}	15		15		ns	

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LC322270J, T-70/80

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Parameter	Symbol	LC322270J,T				Unit	Note
		-70		-80			
		min	max	min	max		
Write command to $\overline{\text{RAS}}$ lead time	t_{RWL}	20		25		ns	
Write command to $\overline{\text{CAS}}$ lead time	t_{CWL}	20		20		ns	
Data input setup time	t_{DS}	0		0		ns	12
Data input hold time	t_{DH}	15		20		ns	12
Data input hold time referenced to $\overline{\text{RAS}}$	t_{DHR}	50		60		ns	
Refresh time	t_{REF}		8		8	ms	
Write command setup time	t_{WCS}	0		0		ns	13
$\overline{\text{CAS}}$ to $\overline{\text{UW}}$, $\overline{\text{LW}}$ delay time	t_{CWD}	50		50		ns	13
$\overline{\text{RAS}}$ to $\overline{\text{UW}}$, $\overline{\text{LW}}$ delay time	t_{RWD}	100		100		ns	13
Column address to $\overline{\text{UW}}$, $\overline{\text{LW}}$ delay time	t_{AWD}	65		65		ns	13
$\overline{\text{CAS}}$ precharge $\overline{\text{UW}}$, $\overline{\text{LW}}$ delay time for fast page mode cycle only	t_{CPWD}	70		70		ns	13
$\overline{\text{CAS}}$ setup time for $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$	t_{CSR}	10		10		ns	
$\overline{\text{CAS}}$ hold time for $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$	t_{CHR}	15		15		ns	
$\overline{\text{RAS}}$ precharge $\overline{\text{CAS}}$ active time	t_{RPC}	10		10		ns	
$\overline{\text{CAS}}$ precharge time for $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ counter test	t_{CPT}	40		40		ns	
$\overline{\text{RAS}}$ hold time referenced to $\overline{\text{OE}}$	t_{ROH}	15		15		ns	
$\overline{\text{OE}}$ access time	t_{OEA}		20		25	ns	9
$\overline{\text{OE}}$ delay time	t_{OED}	15		15		ns	
$\overline{\text{OE}}$ output buffer turn-off delay time	t_{OEZ}	0	15	0	15	ns	10
$\overline{\text{OE}}$ command hold time	t_{OEH}	20		20		ns	
Data input to $\overline{\text{CAS}}$ delay time	t_{DZC}	0		0		ns	16
Data input to $\overline{\text{OE}}$ delay time	t_{DZO}	0		0		ns	16
Masked write setup time	t_{MCS}	0		0		ns	
Masked write hold time referenced to $\overline{\text{RAS}}$	t_{MRH}	0		0		ns	
Masked write hold time referenced to $\overline{\text{CAS}}$	t_{MCH}	0		0		ns	

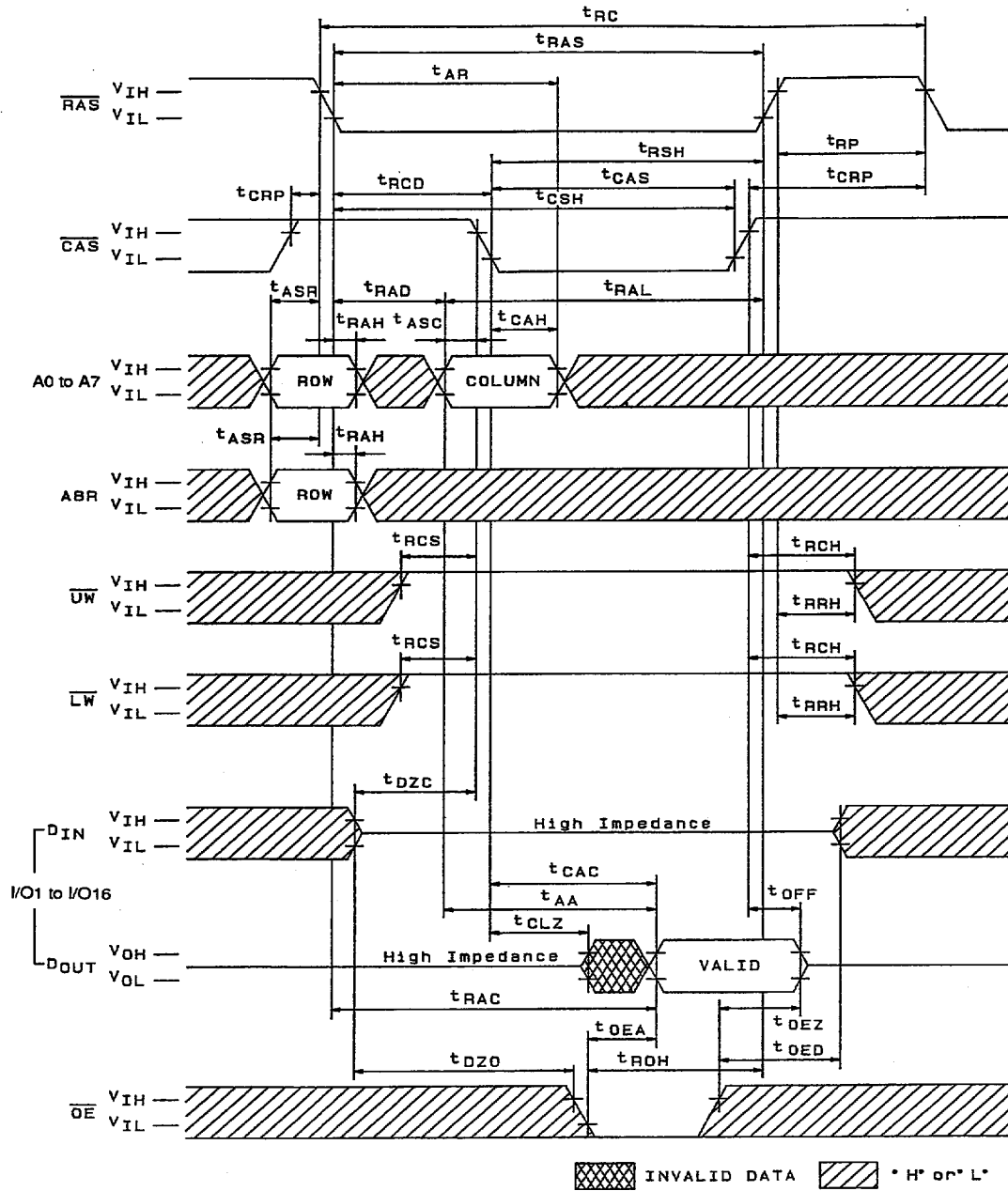
Input/Output Capacitance at $T_a = 25^\circ\text{C}$, $f = 1\text{ MHz}$, $V_{\text{CC}} = 5\text{ V} \pm 10\%$

Parameter	Symbol	min	max	Unit	Note
Input capacitance (A0 to A7 , A8R , $\overline{\text{RAS}}$, $\overline{\text{CAS}}$, $\overline{\text{UW}}$, $\overline{\text{LW}}$, $\overline{\text{OE}}$)	C_{IN}		7	pF	
Input/Output capacitance (I/O1 to I/O16)	C_{IO}		7	pF	

- Note:
6. An initial pause of 200 μs is required after power-up followed by eight $\overline{\text{RAS}}$ -only refresh cycles before proper device operation is achieved. In case of using refresh counter, a minimum of eight $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh cycles instead of eight $\overline{\text{RAS}}$ -only refresh cycles are required.
 7. Measured at $t_T = 5\text{ ns}$.
 8. When measuring input signal timing, V_{IH} (min) and V_{IL} (max) are used for reference points. In addition, rise and fall time are defined between V_{IH} and V_{IL} .
 9. Measured using an equivalent of 50 pF and one standard TTL loads.
 10. t_{OFF} (max) and t_{OEZ} (max) are defined as the time until output voltage can no longer be measured when output switches to a high impedance condition.
 11. Operation is guaranteed if either t_{RRH} or t_{RCH} is satisfied.
 12. These parameters are measured from the falling edge of $\overline{\text{CAS}}$ for an early-write cycle, and from the falling edge of $\overline{\text{UW}}$ and $\overline{\text{LW}}$ for a read-write/read-modify-write cycle.
 13. t_{WCS} , t_{CWD} , t_{RWD} , t_{AWD} and t_{CPWD} are not restrictive operating parameters for memory in that they specify the operating mode. If $t_{\text{WCS}} \geq t_{\text{WCS}}$ (min), the cycle switches to an early-write cycle and output pins switch to high impedance throughout the cycle. If $t_{\text{CWD}} \geq t_{\text{CWD}}$ (min), $t_{\text{RWD}} \geq t_{\text{RWD}}$ (min), $t_{\text{AWD}} \geq t_{\text{AWD}}$ (min) and $t_{\text{CPWD}} \geq t_{\text{CPWD}}$ (min) for fast page mode cycle only, the cycle switches to a read-write/read-modify-write cycle and data output equal information in the selected cells. If neither of the above timings are satisfied, output pins are in an undefined state.
 14. t_{RCD} (max) is not a restrictive operating parameter but instead represents the point at which the access time t_{RAC} (max) is guaranteed. If $t_{\text{RCD}} \geq t_{\text{RCD}}$ (max), access time is determined according to t_{CAC} .
 15. t_{RAD} (max) is not a restrictive operating parameter but instead represents the point at which the access time t_{RAC} (max) is guaranteed. If $t_{\text{RAD}} \geq t_{\text{RAD}}$ (max), access time is determined according to t_{AA} .
 16. Operation is guaranteed if either t_{DZC} or t_{DZO} is satisfied.

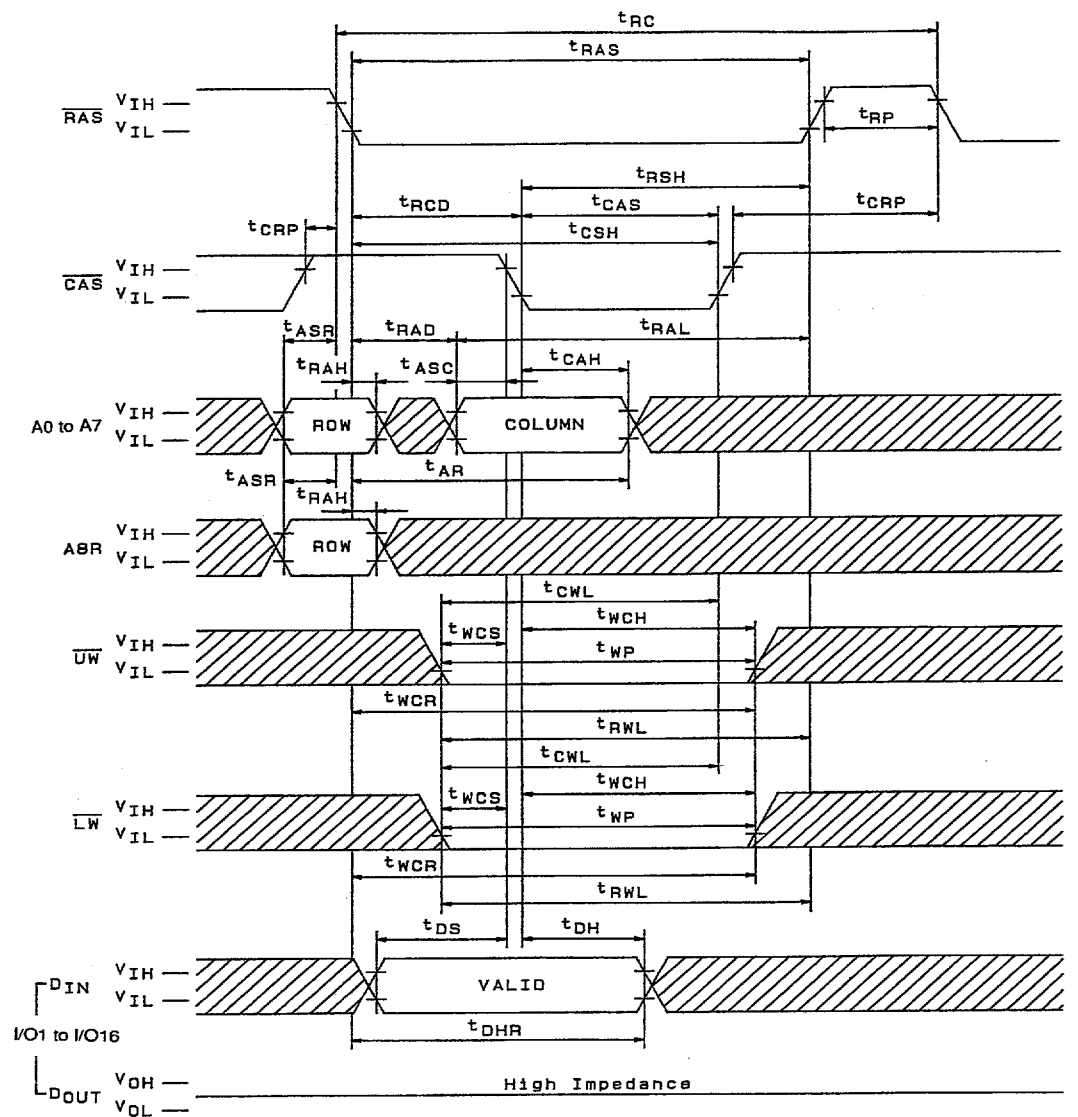
Timing Chart

Read Cycle

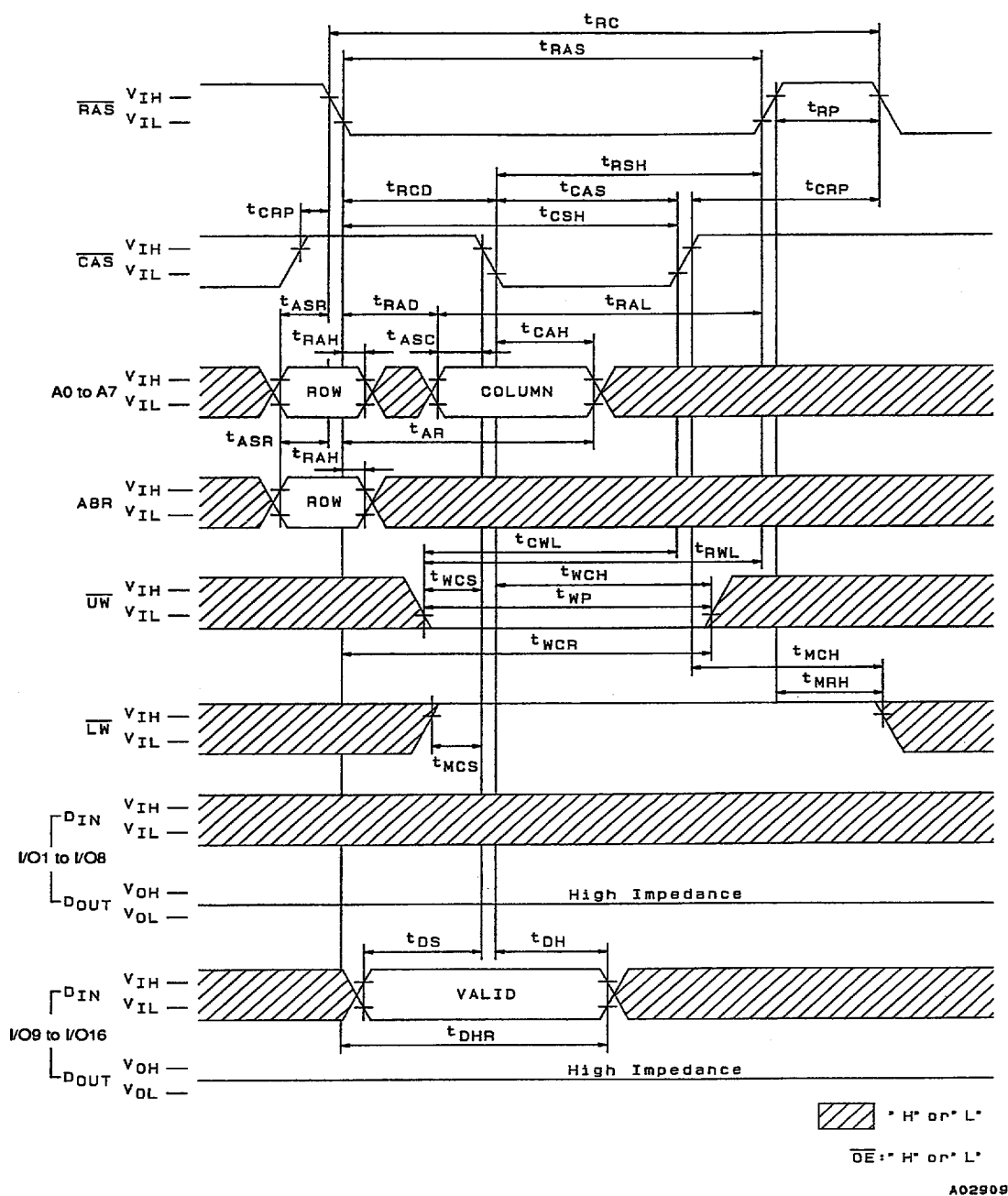


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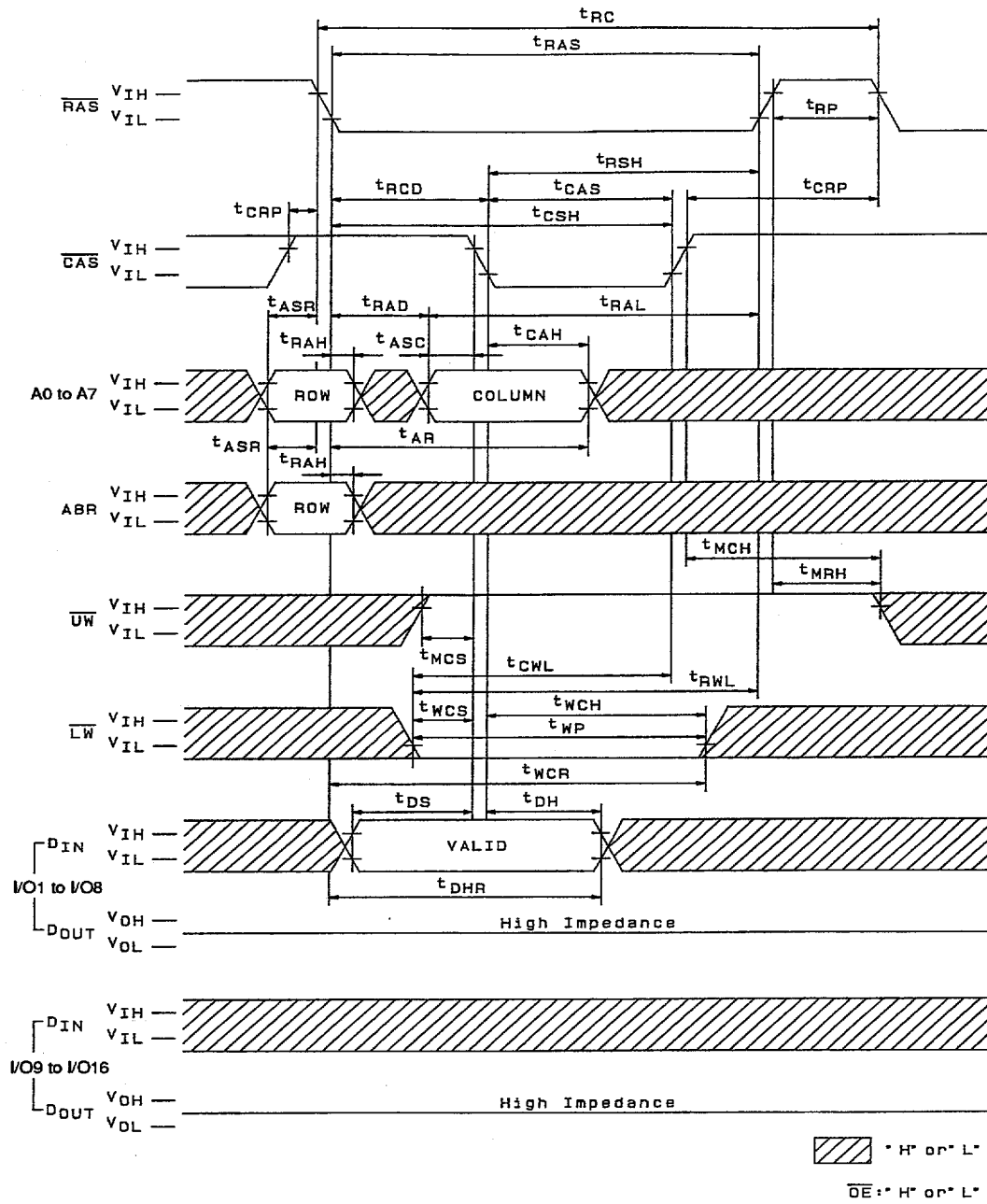
Early Write Cycle



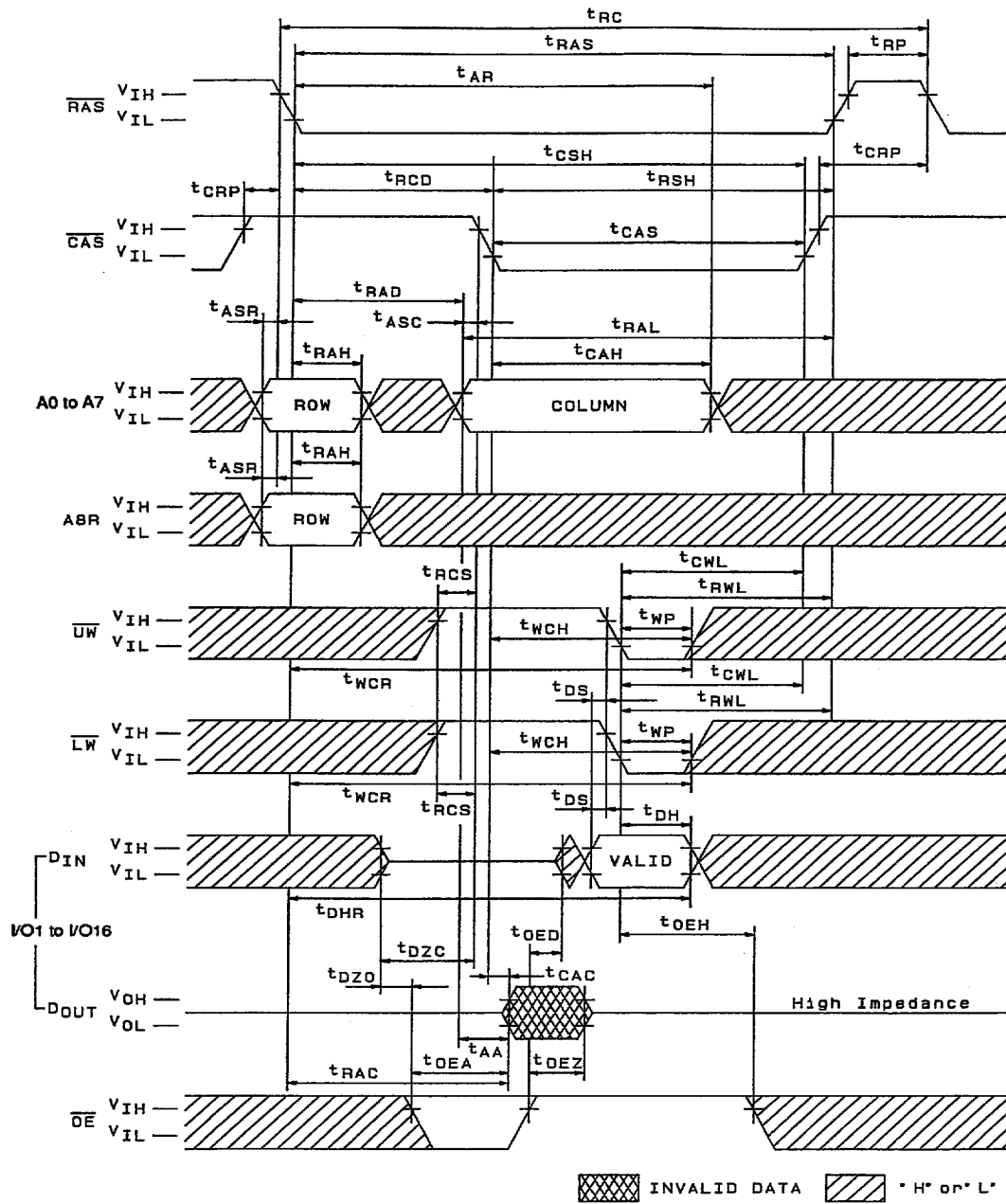
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Lower Byte Early Write Cycle



A02910

Write Cycle ($\overline{OE}$ Control)

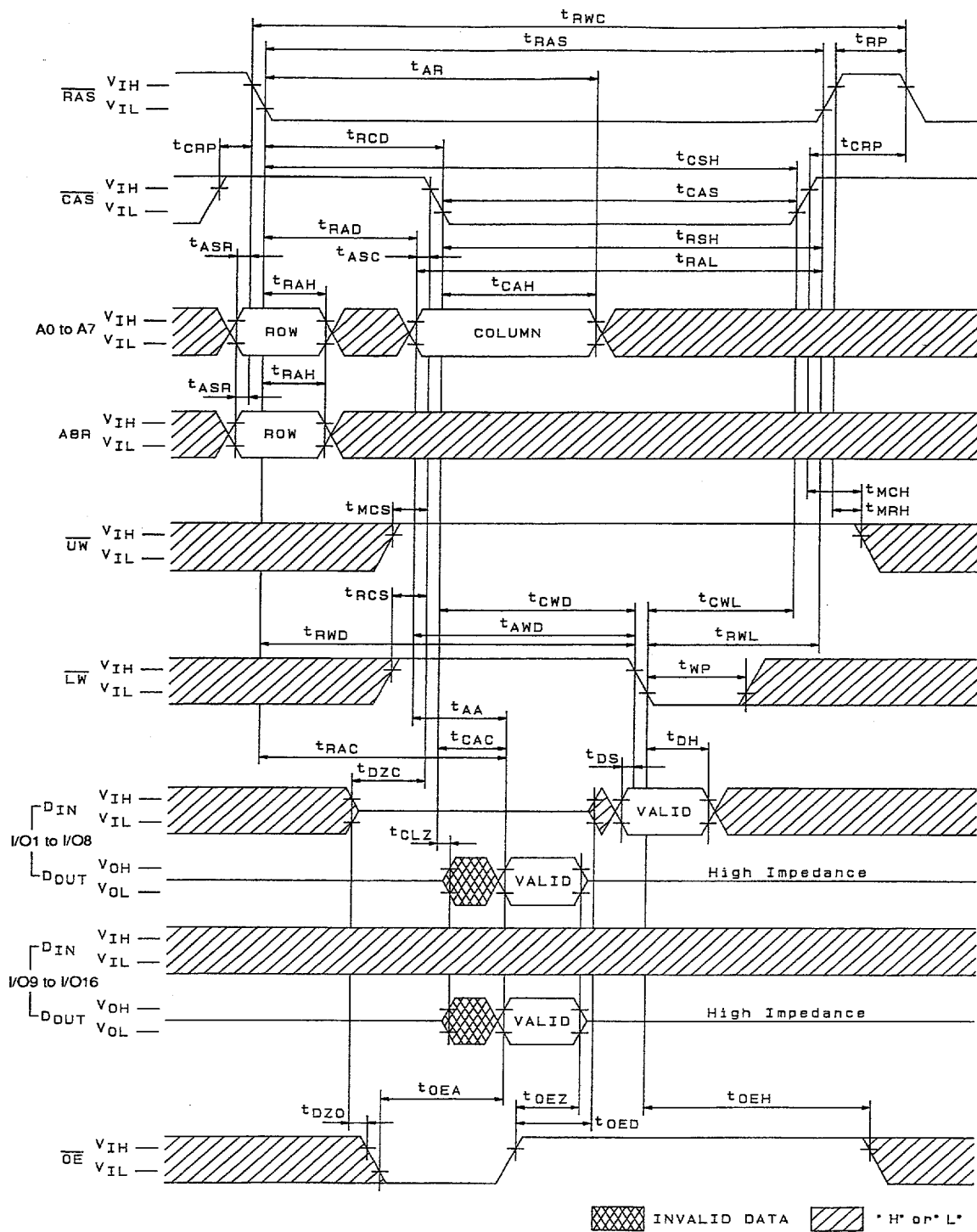
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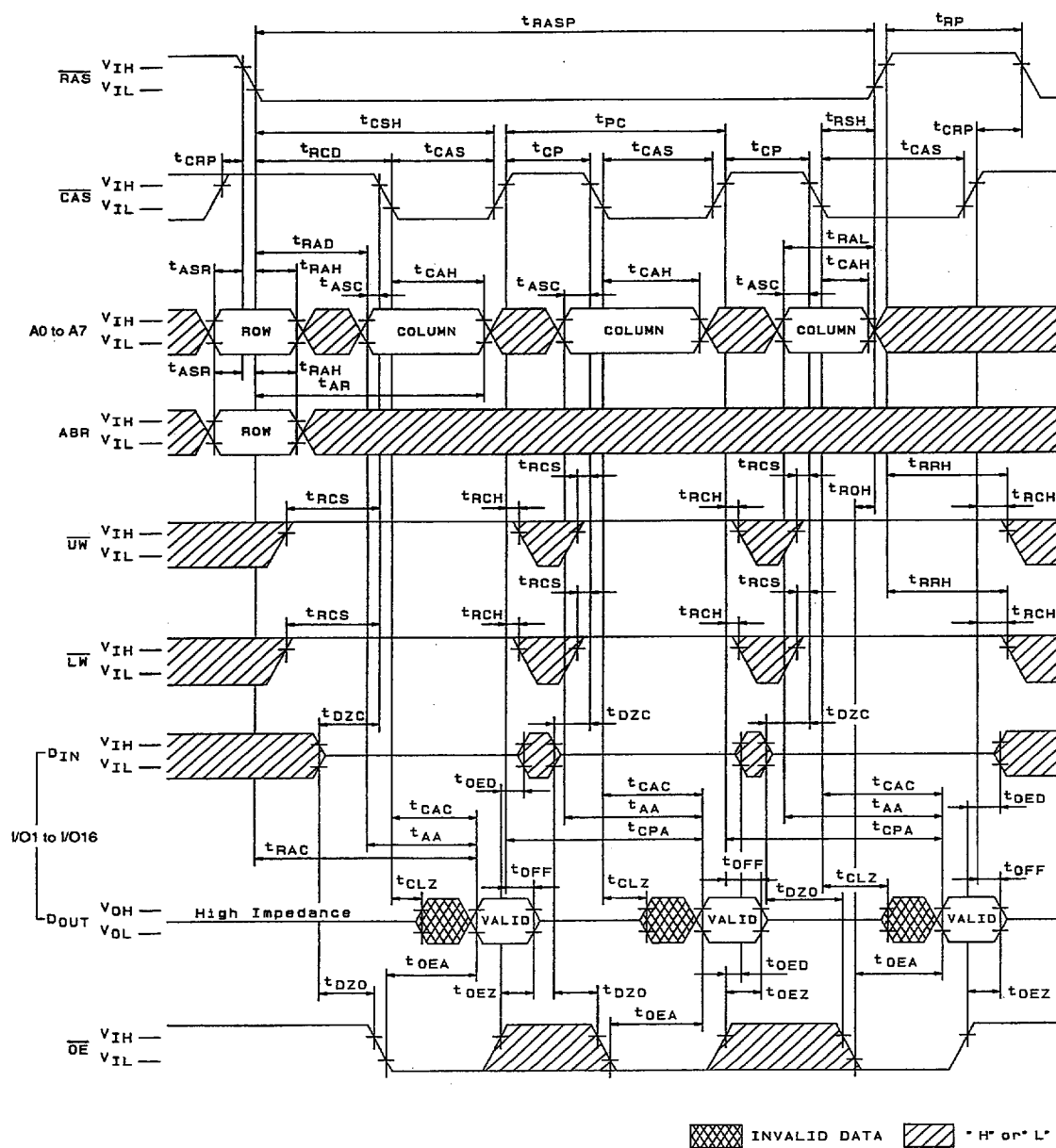


Read-Modify Lower Byte Write Cycle



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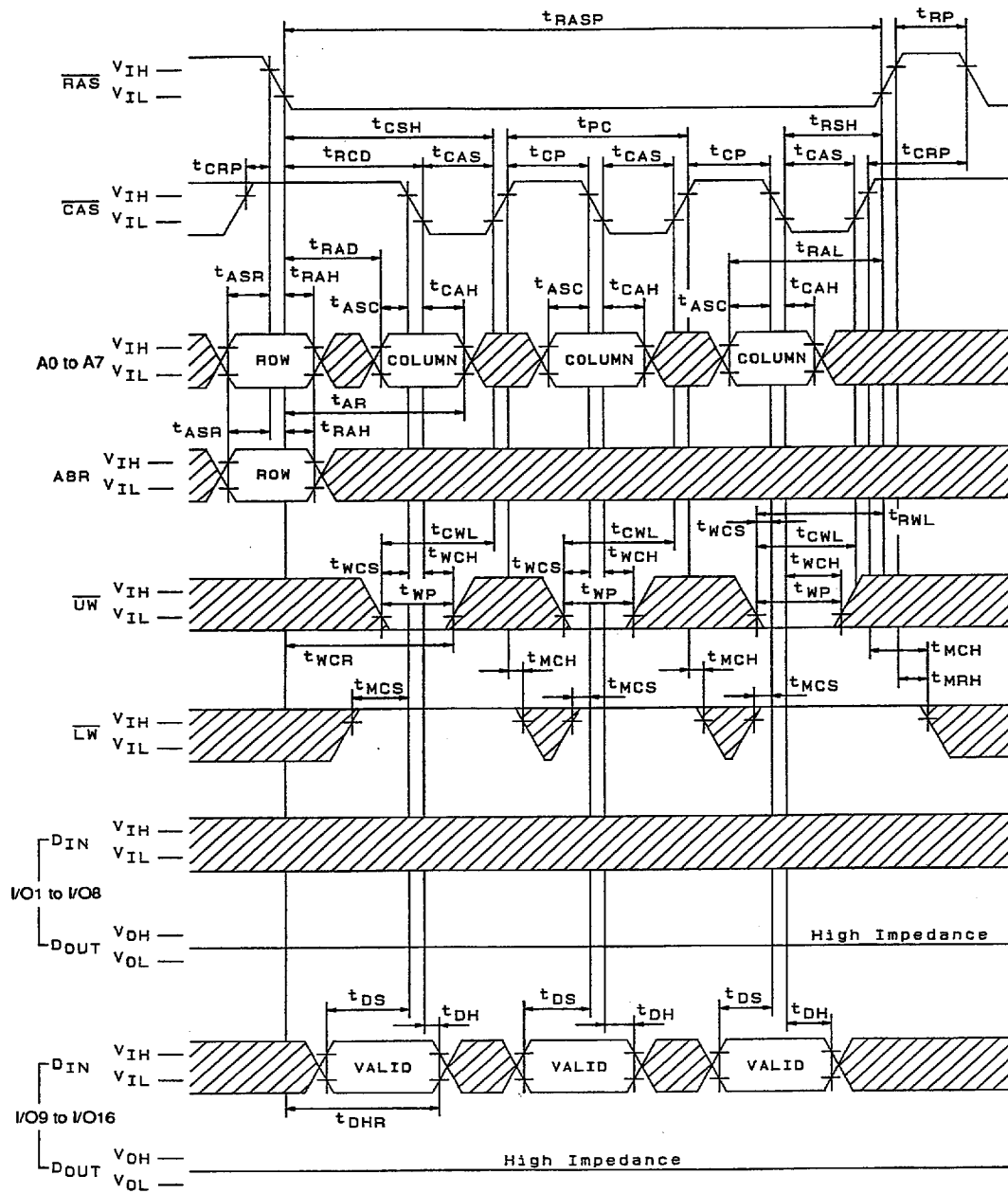
Fast Page Mode Read Cycle



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Fast Page Mode Upper Byte Early Write Cycle



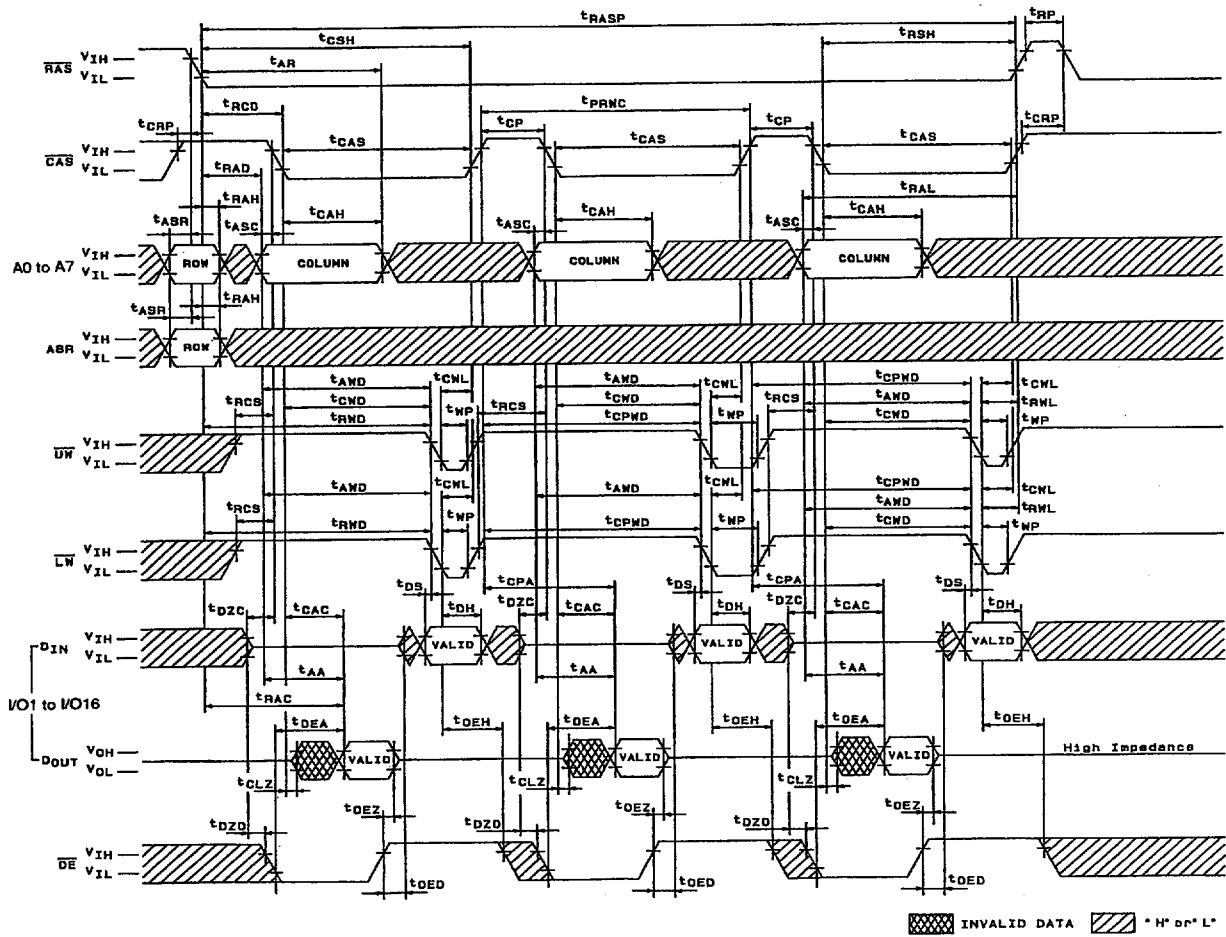
• H* or L*

OE: • H* or L*

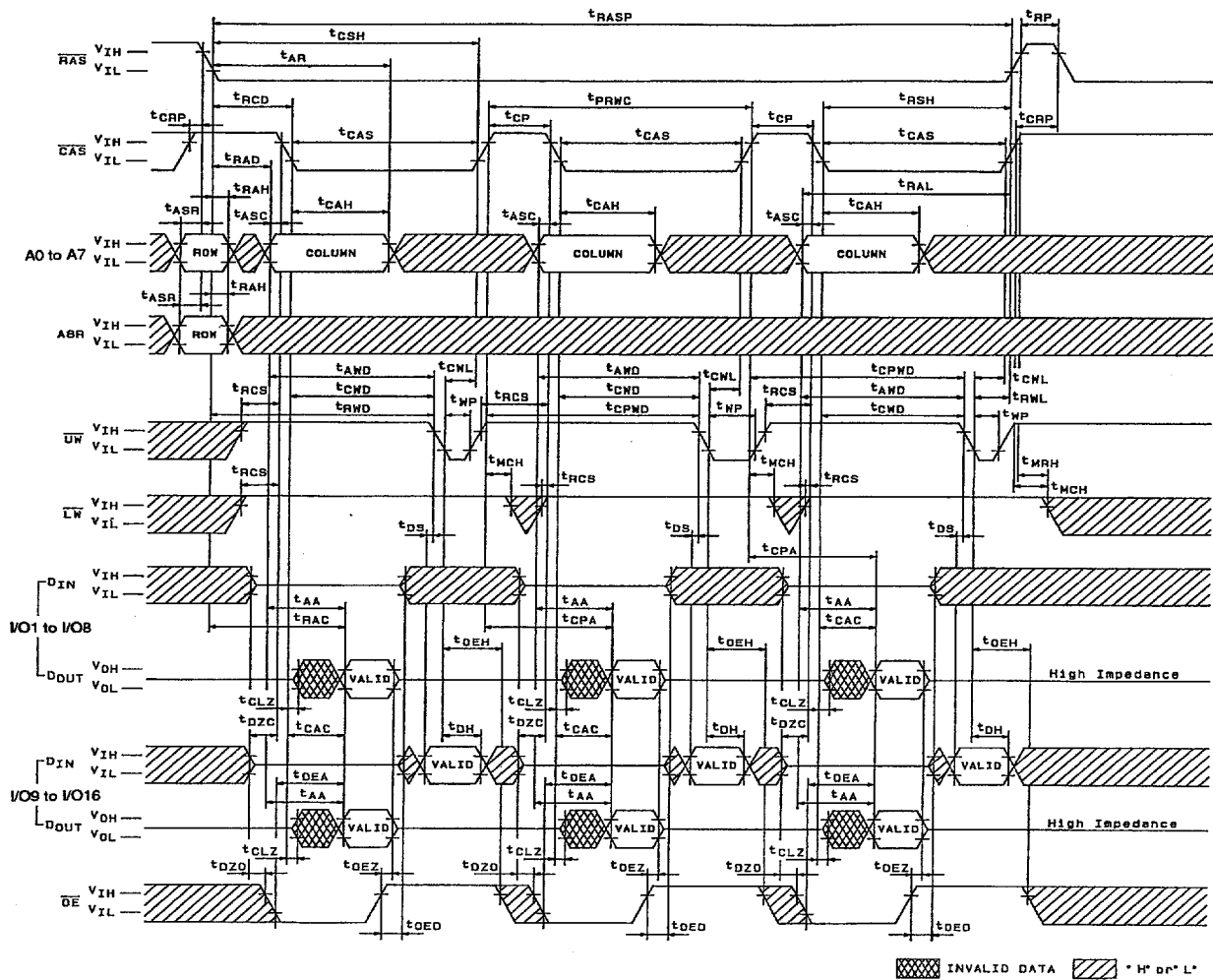
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Fast Page Mode Read-Modify-Write Cycle



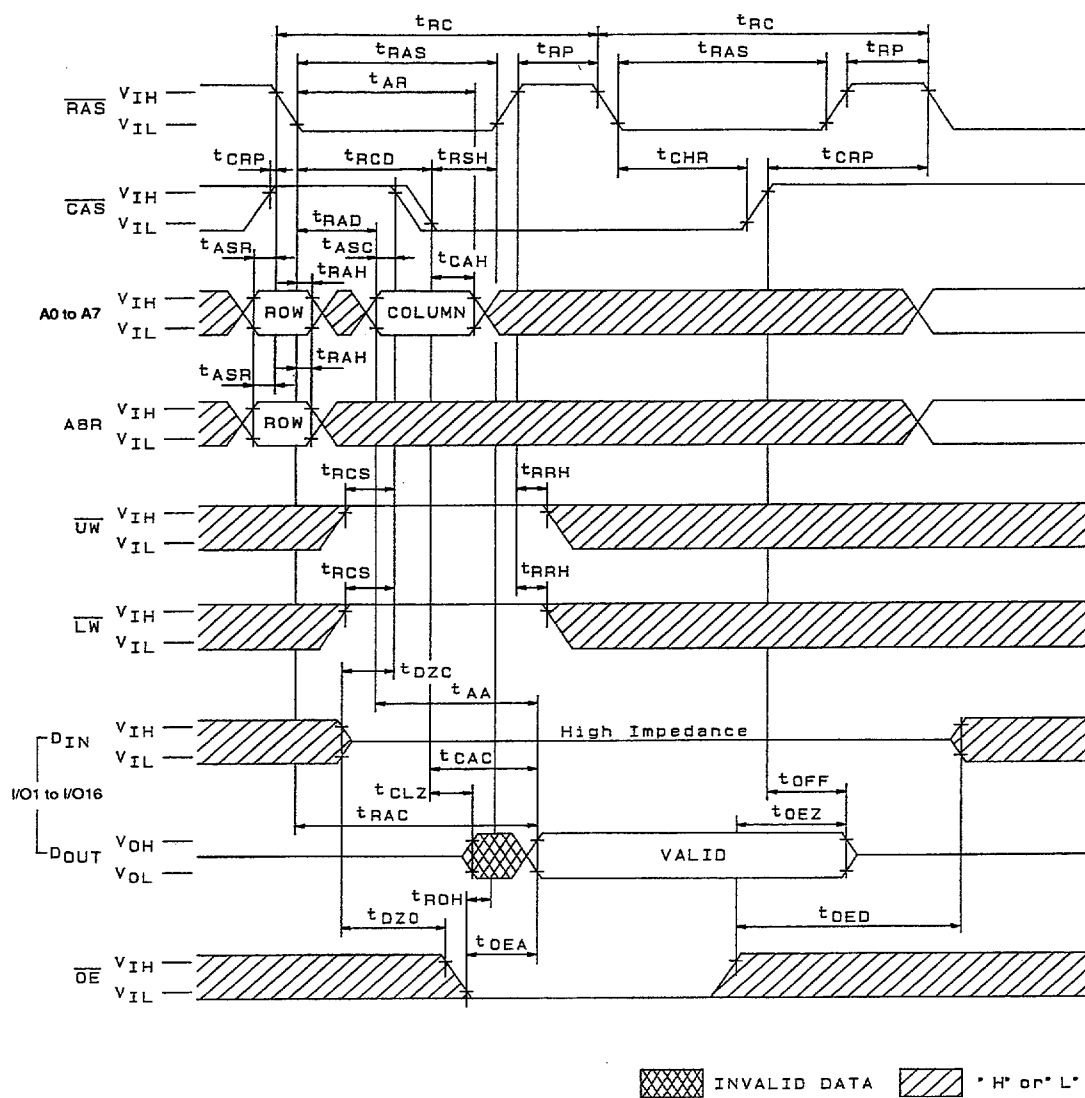
Fast Page Mode Read-Modify Upper Byte Write Cycle



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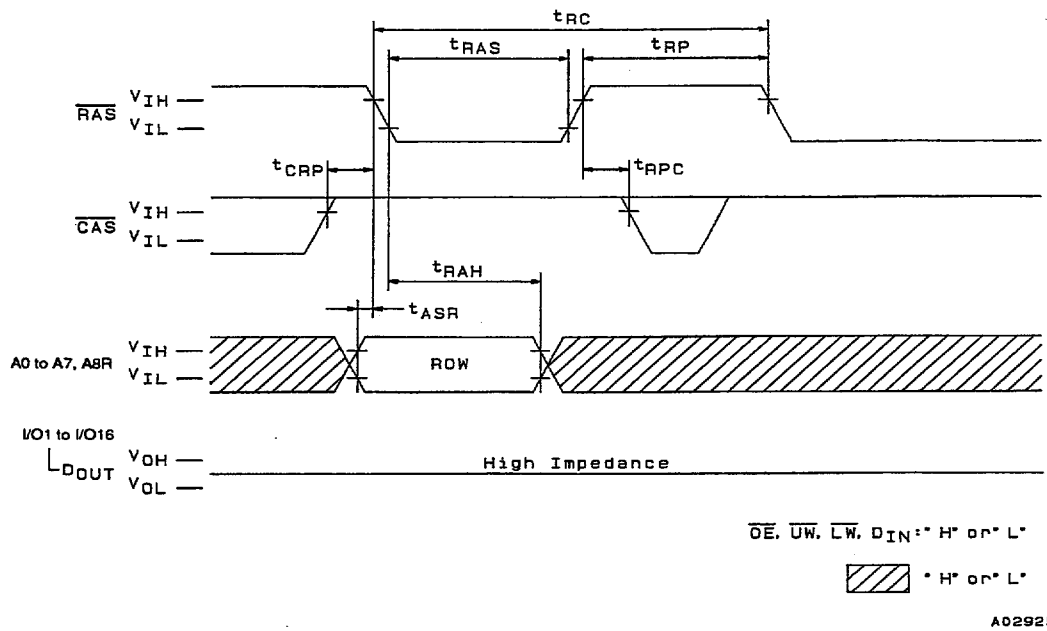


Hidden Refresh Cycle

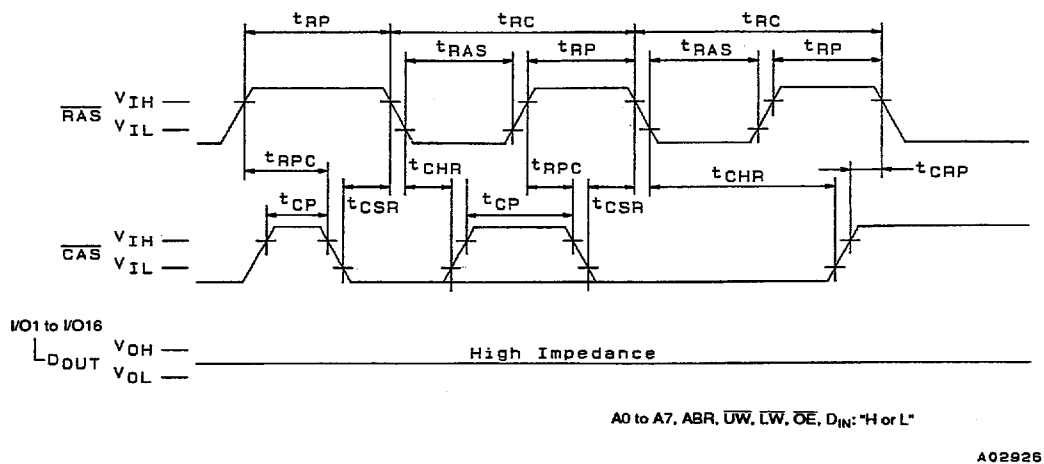


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RAS-Only Refresh Cycle

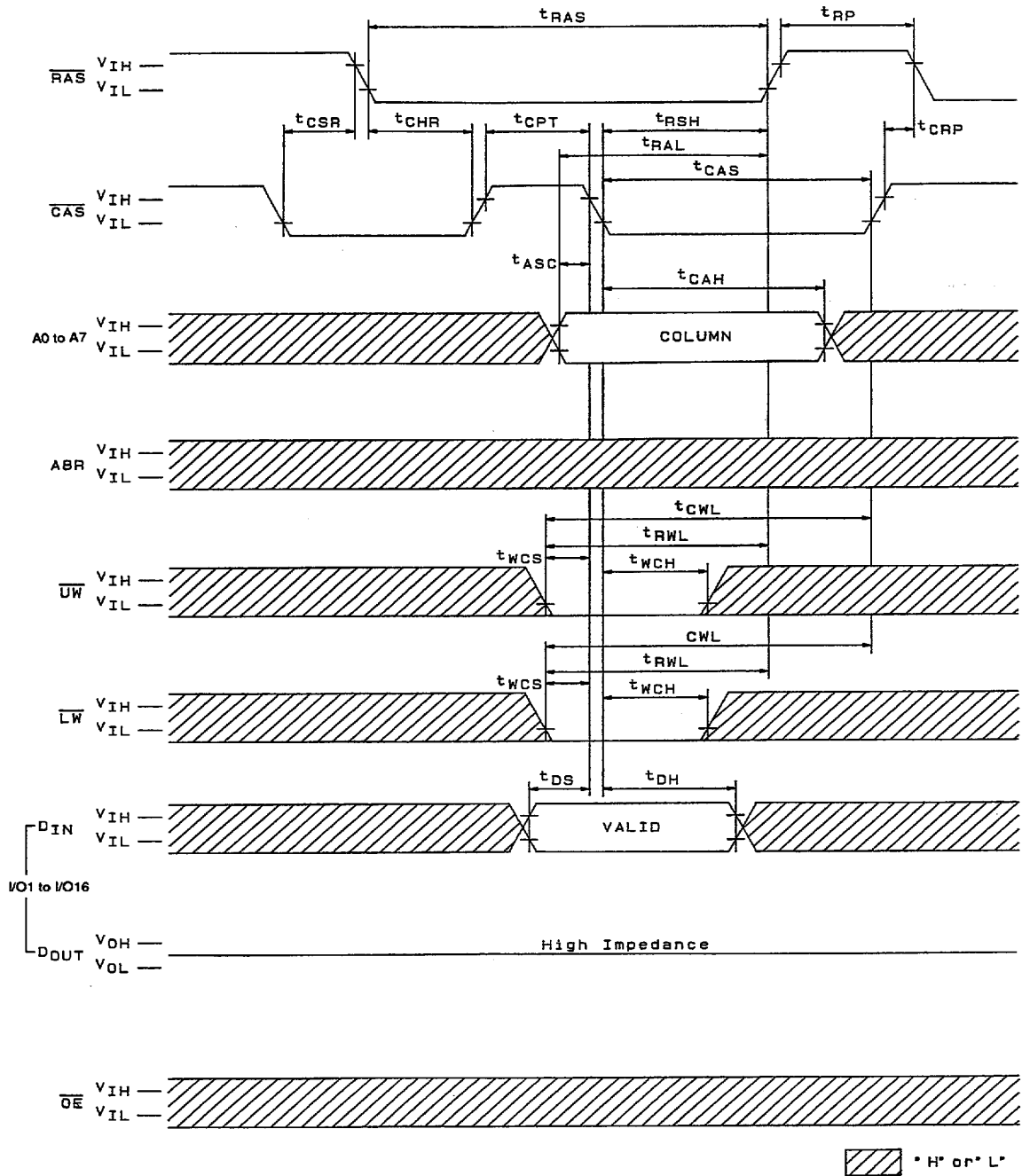


CAS-Before-RAS Refresh Cycle

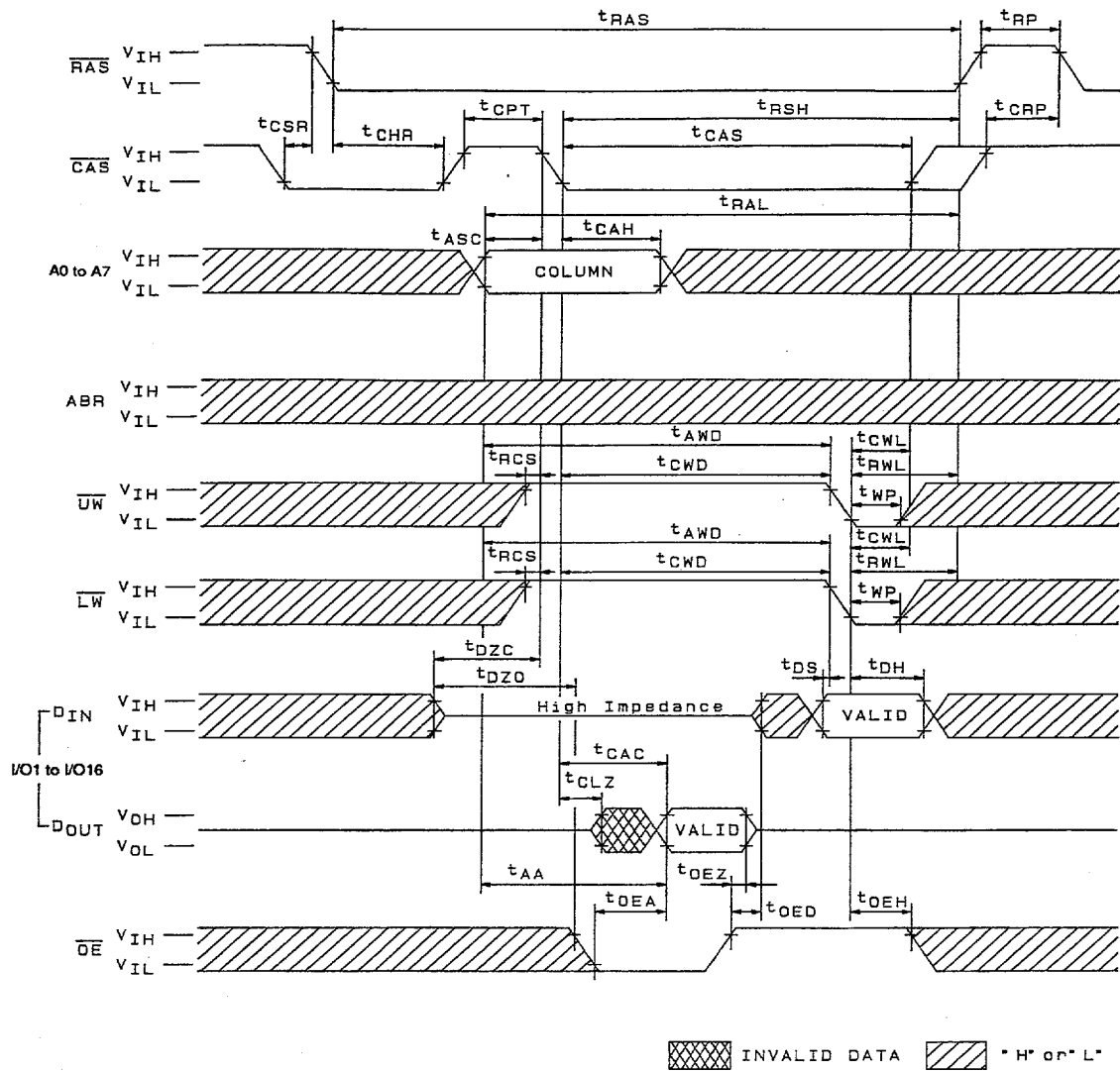




CAS-Before-RAS Refresh Counter Test Cycle (Write)



A02928

CAS-Before-RAS Refresh Counter Test Cycle (Read-Modify-Write)

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